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Strain Engineering for Functional Heterostructures: Aspects of Elasticity

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Summary

- Strain engineering for semiconductor devices or lithium-ion batteries requires a good understanding of elastic effects that strongly influence their functional properties
- **Problems in the modeling of material systems related to:**
- Choice of free energy density with suitable properties
- Dimension reduction for lower-dimensional structures
- In lower-dimensional structures, mathematical challenges arise due to the coupling of mechanical deformation with other physical effects such as electrostatics
-

existence of minimizers: *W* polyconvex [Ball '77], i.e., there exists a convex and lower semi-continuous function $G:\mathbb{R}^{\tau(n)}\to [0,\infty]$ s.t.

 $W(F) = G(T(F)),$ where $T(F) = (F, \det(F), \text{cof}(F), \dots)$

Use variational techniques, e.g., Γ-convergence, combined with modern tools for nonlinear partial differential equations

smoothness and non-interpenetration: W ∈ *C* [∞](R *n*×*n*) or $W \in C^\infty(\mathbb{R}^{n \times n} \cap {\text{det}} > 0)$ and $W(F) \to \infty$ as $\det F \to 0$

Polyconvex energy densities with generic elastic constants

Modeling assumptions for free energy density $W : \mathbb{R}^{n \times n} \to [0, \infty]$: $$ ■ *material symmetry:* For the point group $P \subseteq O(n)$

 $W(P^TFP) = W(F)$ for all $P \in \mathcal{P}$ and all $F \in \mathbb{R}^{n \times n}$

 \blacksquare normalization: $W(F) \geq 0$ and $[W(F) = 0 \Longleftrightarrow F \in SO(n)]$

Result [Conti, Lenz & Zwicknagl, in preparation]: Let P be a subgroup of $O(n)$, $\mathbb{C}: \mathbb{R}^{n \times n} \to \mathbb{R}^{n \times n}$ linear, symmetric s.t. $\mathbb{C}\xi:\xi\geq\tilde{\bm{c}}|\xi+\xi^{\mathsf{T}}$ | 2, $\mathbb{C}(\xi - \xi^T) = 0$ for all $\xi \in \mathbb{R}^{n \times n}$, $\mathbb{C}(R\xi R^{T}): (R\xi R^{T}) = \mathbb{C}\xi : \xi$ for all $\xi \in \mathbb{R}^{n \times n}$, $R \in P$.

Rigorous dimension reduction via Γ**-convergence** Thin structures with thickness 0 < *h* ≪ 1 plates Ω plate $h^{\text{plate}} = \omega \times$ $\sqrt{2}$ − *h* 2 $, +\frac{h}{2}$ 2 \setminus $, \quad \omega \subset \mathbb{R}^{n-1}$

> $\text{roots} \qquad \Omega_h^{\text{rod}} = (0, L) \times hS, \qquad \qquad S \subset \mathbb{R}$ $S \subset \mathbb{R}^{n-1}$

Finite-strain electro-mechanical model for deformation *v* and electric potential φ

 $-\text{div}((\text{det }M(x)\partial_F W(\nabla vM(x)^{-1})M(x)^{-T}-h^{\alpha}\text{div}\mathfrak{H}(\nabla^2 v))=0,$ $-div(A(x, \nabla v)\nabla \varphi) = q(x),$

linearization and measured elastic constants:

1

$$
W(\mathsf{Id} + \varepsilon) = W(\mathsf{Id}) + DW(\mathsf{Id})\varepsilon + \frac{1}{2}D^2W(\mathsf{Id})[\varepsilon, \varepsilon] + o(|\varepsilon|^2)
$$

=
$$
\frac{1}{2}\sum_{\mathsf{i} j \mathsf{k} l} \mathbb{C}_{\mathsf{i} j \mathsf{k} l} \varepsilon_{\mathsf{i} j} \varepsilon_{\mathsf{k} l} + o(|\varepsilon|^2)
$$

 \blacksquare hyperstress regul. $\mathfrak H$ leads to 2nd-grade nonsimple materials prestrain $M(x) \in \mathbb{R}^{n \times n}$ models lattice mismatch in heterostructures $A(x, F) = (\det F) F^{-1} a(x) F^{-\top}, F = \nabla v$, is the pulled-back dielectric coefficient, $a \in L^{\infty}(\Omega_h)$ such that $a(x) \ge a_0 > 0$ a.e. in Ω_h , fixed charge density *q* ∈ *L* [∞](Ω*h*)

Typical approaches in the literature

- linear elastic energy density evaluated at nonlinear strains [**?**], which leads to non-polyconvex *W*
- specific ansatz using structural tensors \rightarrow restrictions on elastic constants

Then,

(i) there is a polyconvex function $W \in C^\infty(\mathbb{R}^{n \times n}; [0, \infty))$ s.t.

- simulations using finite element methods
- **significant potential of strain to influence** piezoelectricity and electronic band structure 1 Weierstrass Institute for Applied Analysis and Stochastics, Mohrenstr. 39, 10117 Berlin

Idea of the proof: Use linear elastic energy density evaluated at nonlinear strain near *SO*(*n*), and construct explicit polyconvex extension using curvature of *SO*(*n*).

- **Application: semiconductor/perovskite/semiconductor** heterostructures for perovskite solar cells belong to a class of crystalline semiconductors and have several advantages like adjustable band gaps, high absorption coefsolar cells beat the efficiency of the widely used silicon solar cells under laboratory conditions [9]. The diffusion engineering
- **. analysis of drift-diffusion models including the migration of ions:** existence of weak solutions, boundedness [?], and uniqueness and give of annear design induction ionic variety and imgration c and holes also the movement of ionic vacancies in the perovskite material.

System has saddle-point structure with energy functional

$$
\mathcal{E}_h(v, \varphi) = \mathcal{E}_h^{\text{mech}}(v) - \mathcal{E}_h^{\text{elec}}(v, \varphi)
$$

=
$$
\int_{\Omega_h} W(\nabla v M^{-1}) \det M + h^{\alpha} H(\nabla^2 v) + q\varphi - \frac{1}{2} A(\nabla v) \nabla \varphi \cdot \nabla \varphi dx
$$

Work in progress: Limit passage for $h \to 0$ for thin plate in the bending regime, i.e., for the scaling $\widetilde{\mathcal{E}}_h = \frac{1}{h^2}$ *h* ²E*^h* via Γ-convergence methods. At the first stage, we have proved the $Γ$ – convergence result for bending model with prestrain coupled by the Poisson equation without deformation, $\nabla v = id$, and with isotropic permeability.

Outlook: Investigate rod model and different scaling regimes.

Strain distribution in zincblende and wurtzite GaAs nanowires

Cooperations Perovskite Silicon Tandem Solar Cell (Fraunhofer ISE, Freiburg), Perovskite unit cell, Current-Voltage-Characteristics

nathematical model for heterostructures reacting on strain caused by lattice mismatch [**?**] non-linear elasticity with local prestrain

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- A. M. A. GiO QOO A weeke been to set be **AMaSiS 2024 workshop together with PaA-1, AA2-13, AA2-17**
- \overline{a} Cinita atroin hyperalecticity in hattery models with. **Finite-strain hyperelasticity in battery models with PaA-2**

 $W(\xi) \geq c \text{ dist}^2$ $(\xi, SO(n)),$ min $W = W(d) = 0, D^2W(d) = \mathbb{C}$ and $W(QR^T \xi R) = W(\xi)$ for all $Q \in SO(n)$, $R \in P$, $\xi \in \mathbb{R}^{n \times n}$. (ii) there is a polyconvex function $W \in C^\infty(\mathbb{R}^{n \times n} \cap \{\det > 0\}; [0, \infty))$ s.t. $W(\xi) \rightarrow \infty$ as det $\xi \rightarrow 0$ and (i) holds.

Vacancy assisted charge transport (with PaA-1)

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